

AK Trench-FS IGBT

Features

- Trench FS technology
- Low $V_{CE(sat)}$
- Low EMI

Application

- Converters
- Power drivers

Recommended

- Power modules, such as Easy PACK, Econo PACK etc

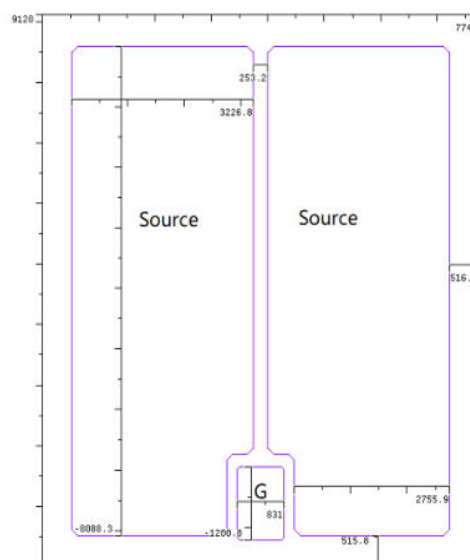
1200V75A Trench FS IGBT

Parameter	Value	Unit
V_{CE}	1200	V
I_C	75	A
$V_{CE(sat)}$ at $I_C=75A$ (Wafer level test)	1.9	V

Wafer Size (inch)	8
Chip Size with scribe (mm ²)	7.82 x 9.2
Wafer Thickness (um)	120±10
Gate PAD Size (mm ²)	0.831 x 1.2
Emitter PAD Size (mm ²)	3.226 x 8.088
Top Metal	AlCu
Top Metal Thickness (µm)	5
Back Metal	Al/Ti/Ni/Ag
Scribe Line (µm)	80
Passivation	Polyimide
Gross Die	356
Recommended Storage Environment	Store in original container, in dry nitrogen, <3months at an ambient temperature of 23±3°C

Unit: um

Die Size Without 80um scribe line



Maximum Ratings (T_j=25°C, unless otherwise specified)

Parameter	Symbol	Value	Unit	
Collector-emitter voltage	V _{CE}	1200	V	
Gate-emitter voltage	V _{GE}	+/-20	V	
DC collector current	I _C	T _j =25°C	150	A
		T _j =100°C	75	
Pulsed collector current	I _{CM}	225	A	
Short circuit withstand time (V _{GE} =15V, V _{CC} =600V)	t _{SC}	20	us	
Junction temperature range	T _{vj}	-40~+175	°C	
Operating junction temperature	T _{vjop}	-40~+150	°C	

Electrical Characteristics at T_j=25°C (unless otherwise specified)

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Static Characteristic (Test on wafer)						
Collector-emitter breakdown voltage	V _{(BR)CES}	V _{GE} =0V, I _C =1mA	1200	-	-	V
Gate-emitter threshold voltage	V _{GE(th)}	I _C =2.6mA, V _{CE} =V _{GE}	5	5.8	6.6	V
Collector-emitter saturation voltage	V _{CE(sat)}	V _{GE} =15V, I _C =75A	-	1.9	2.25	V
Gate leakage current	I _{GES}	V _{CE} =0V, V _{GE} =+/-20V	-	-	500	nA
Collector leakage current	I _{CES}	V _{CE} =1200V, V _{GE} =0V	-	-	250	uA
Integrated gate resistor	R _G		-	10	-	Ω
Dynamic Characteristic ^(a)						
Input capacitance	C _{ies}	V _{GE} =0V, V _{CE} =25V f=1MHz	-	5200	-	pF
Output capacitance	C _{oes}		-	240	-	pF
Reverse transfer capacitance	C _{res}		-	215	-	pF
Gate charge	Q _g	V _{CC} =960V, I _C =75A V _{GE} =15V	-	365	-	nC

(a) Dynamic and switching test data depending on TO264 package, not subject to production test